Abstract of The Disclosure

In order to make preparation of a semiconductor material having a high conductance possible by increasing a carrier concentration even in a case where a crystal layer is doped with p-type impurity raw materials and n-type impurity raw materials, an impurity doping method for semiconductor wherein a crystal layer made of crystal raw materials is doped with impurities, comprises each of plural types of impurity raw materials being supplied at close timings in a pulsed manner within one cycle wherein all types of the crystal raw materials are supplied in one time each in the case when plural types of the crystal raw materials are alternately supplied in a pulsed manner with maintaining each of predetermined purge times.